NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI MRF374** is Designed for broadband commercial and industrial applications in 470 to 860 MHz band.

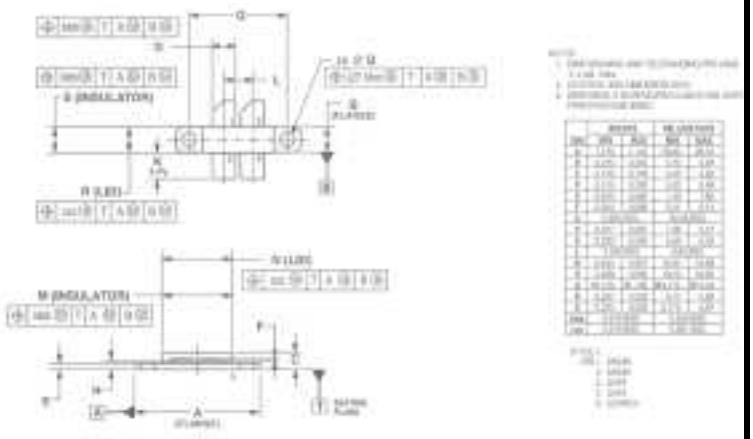
FEATURES:

- **P_G =** 13.5 dB typ. at 100 W/875 MHz
- η_D = 36 % Typical
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_D	7.0 A
V_{DSS}	65 V
V_{GS}	±20 V
P_{DISS}	270 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.65 °C/W

PACKAGE STYLE .230 BAL FLG.



CHARACTERISTICS T_C = 25 ° C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_{DSS}	I_{DS} = 1.0 µA		65			V
I_{DSS}	V_{DS} = 28 V				1.0	µA
I_{GSS}	V_{GS} = 20 V				1.0	µA
$V_{GS(th)}$	V_{DS} = 10 V	I_D = 200 µA	2.0	3.5	4.0	V
$V_{GS}(Q)$	V_{DS} = 28 V	I_D = 100 mA	3.0	4.2	5.0	V
$V_{DS(ON)}$	V_{DS} = 10 V	I_D = 3.0 A		0.56	0.8	V
G_{FS}	V_{DS} = 10 V	I_D = 3.0 A	2.2	2.8		S

Specifications are subject to change without notice.

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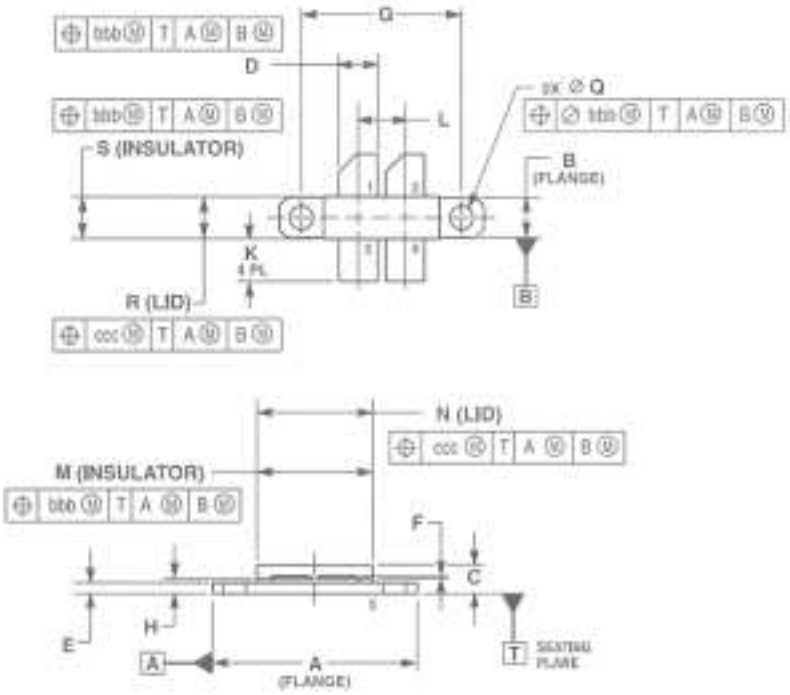
CHARACTERISTICS $T_C = 25\,^\circ C$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
C_{ISS} C_{OSS} C_{RSS}	V_{DS} = 28 V V_{GS} = 0 V f = 1.0 MHz		80 45 3.5		pF
P_G η_D IMD VSWR	V_{DD} = 28 V I_{DQ} = 400 mA P_{OUT} = 100 W f1 = 857 MHz, f2 = 863 MHz	12.5 30 -28	13.5 36 -31 5:1		dB % dB ---
P_G η_D IMD	V_{DD} = 28 V I_{DQ} = 500 mA P_{OUT} = 100 W f1 = 857 MHz, f2 = 863 MHz		12 36 -34		dB % dB



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